

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-30V	0.185Ω	-2.0A

Description

This new generation of high density MOSFETs from Diodes Incorporated utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

Features

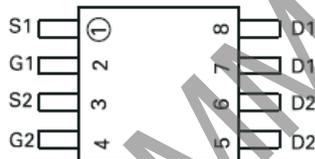
- Low On-resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Profile SOIC Package

Applications

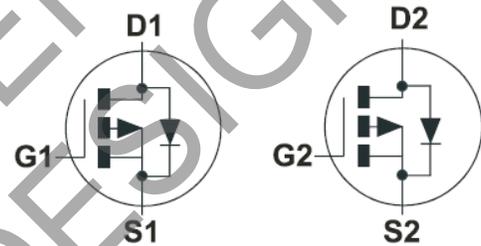
- DC - DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control



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Pin-out
Top View



P-channel

Ordering Information

Part Number	Device Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXMD63P03XTA	ZXM63P03	7	12mm Embossed	1000 Units
ZXMD63P03XTC	ZXM63P03	13	12mm Embossed	4000 Units

Absolute Maximum Ratings

PARAMETER	SYMBOL	P-CHANNEL	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($V_{GS}=-4.5V, T_A=25^\circ C$) (b) (d) ($V_{GS}=-4.5V, T_A=70^\circ C$) (b) (d)	I_D	-2.0 -1.6	A A
Pulsed Drain Current (c)(d)	I_{DM}	-9.6	A
Continuous Source Current (Body Diode)(b)(d)	I_S	-1.4	A
Pulsed Source Current (Body Diode)(c)(d)	I_{SM}	-9.6	A
Power Dissipation at $T_A=25^\circ C$ (a)(d) Linear Derating Factor	P_D	0.87 6.9	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (a)(e) Linear Derating Factor	P_D	1.04 8.3	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b)(d) Linear Derating Factor	P_D	1.25 10	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

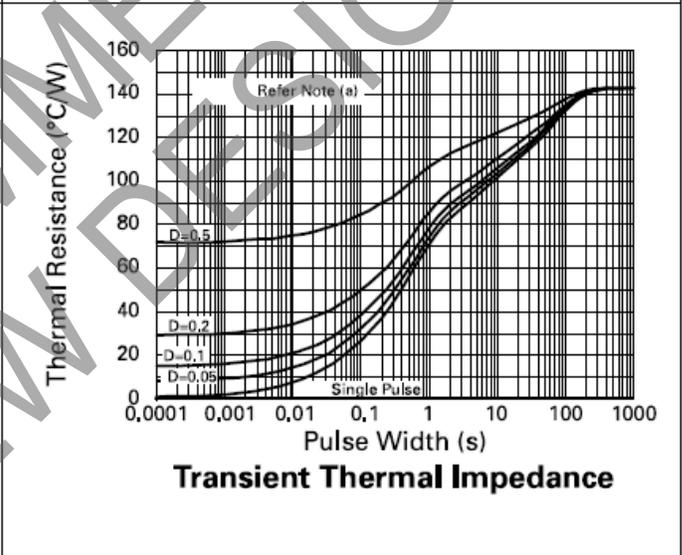
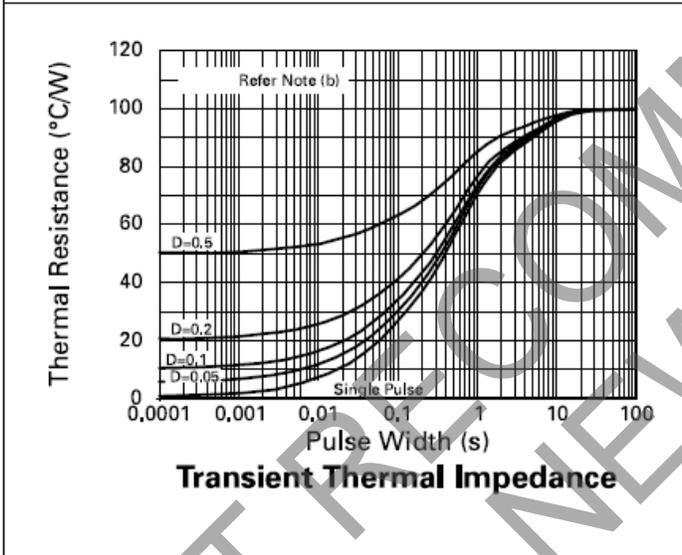
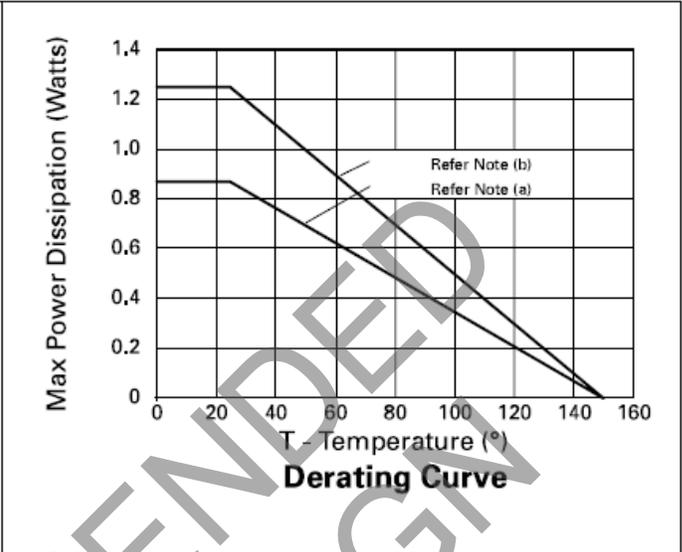
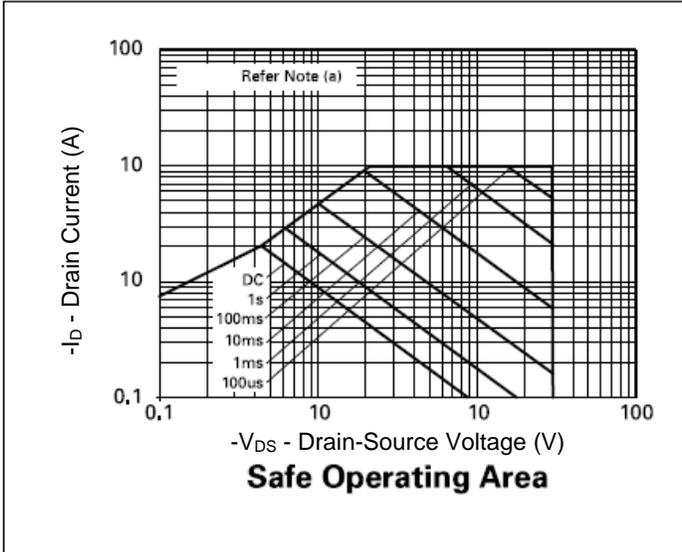
Thermal Resistance

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	143	$^\circ C/W$
Junction to Ambient (b)(d)	$R_{\theta JA}$	100	$^\circ C/W$
Junction to Ambient (a)(e)	$R_{\theta JA}$	120	$^\circ C/W$

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
 (b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.
 (c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
 (d) For device with one active die.
 (e) For device with two active die running at equal power.

Characteristics



NOT FOR NEW DESIGN

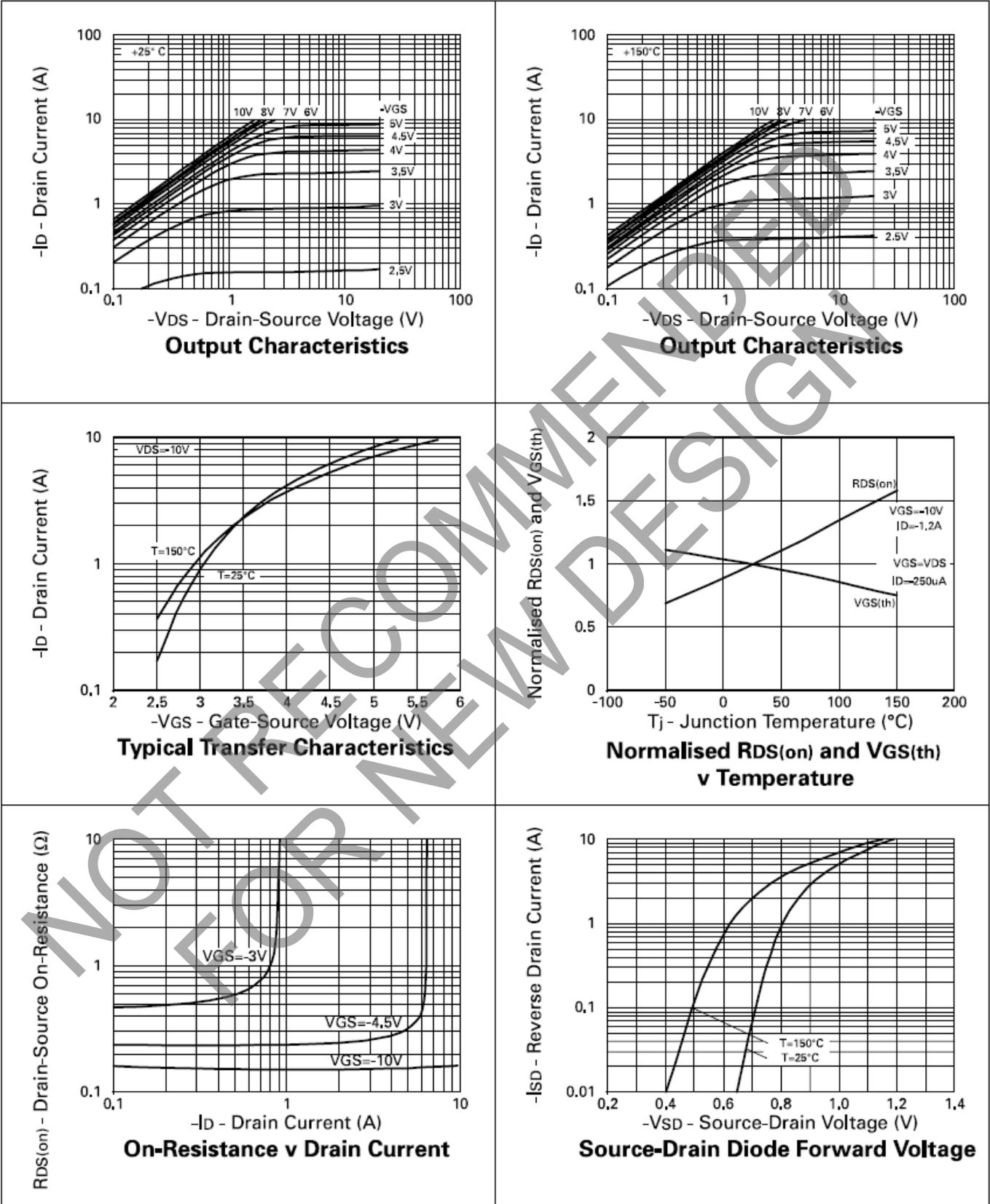
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	V _{DS} =-30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			± 100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	I _D =-250μA, V _{DS} =V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.185 0.27	Ω	V _{GS} =-10V, I _D =-1.2A V _{GS} =-4.5V, I _D =-0.6A
Forward Transconductance (3)	g _{fs}	0.92			S	V _{DS} =-10V, I _D =-0.6A
DYNAMIC (3)						
Input Capacitance	C _{iss}		270		pF	V _{DS} =-25 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		80		pF	
Reverse Transfer Capacitance	C _{rss}		30		pF	
SWITCHING (2) (3)						
Turn-On Delay Time	t _{d(on)}		2.6		ns	V _{DD} =-15V, I _D =-1.2A R _G =6.2Ω, R _D =6.2Ω (Refer to test circuit)
Rise Time	t _r		4.8		ns	
Turn-Off Delay Time	t _{d(off)}		13.1		ns	
Fall Time	t _f		9.3		ns	
Total Gate Charge	Q _g			7	nC	
Gate-Source Charge	Q _{gs}			1.2	nC	V _{DS} =-24V, V _{GS} =-10V, I _D =-1.2A (Refer to test circuit)
Gate Drain Charge	Q _{gd}			2	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			-0.95	V	T _J =25°C, I _S =-1.2A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		21.4		ns	T _J =25°C, I _F =-1.2A, di/dt= 100A/μs
Reverse Recovery Charge(3)	Q _{rr}		15.7		nC	

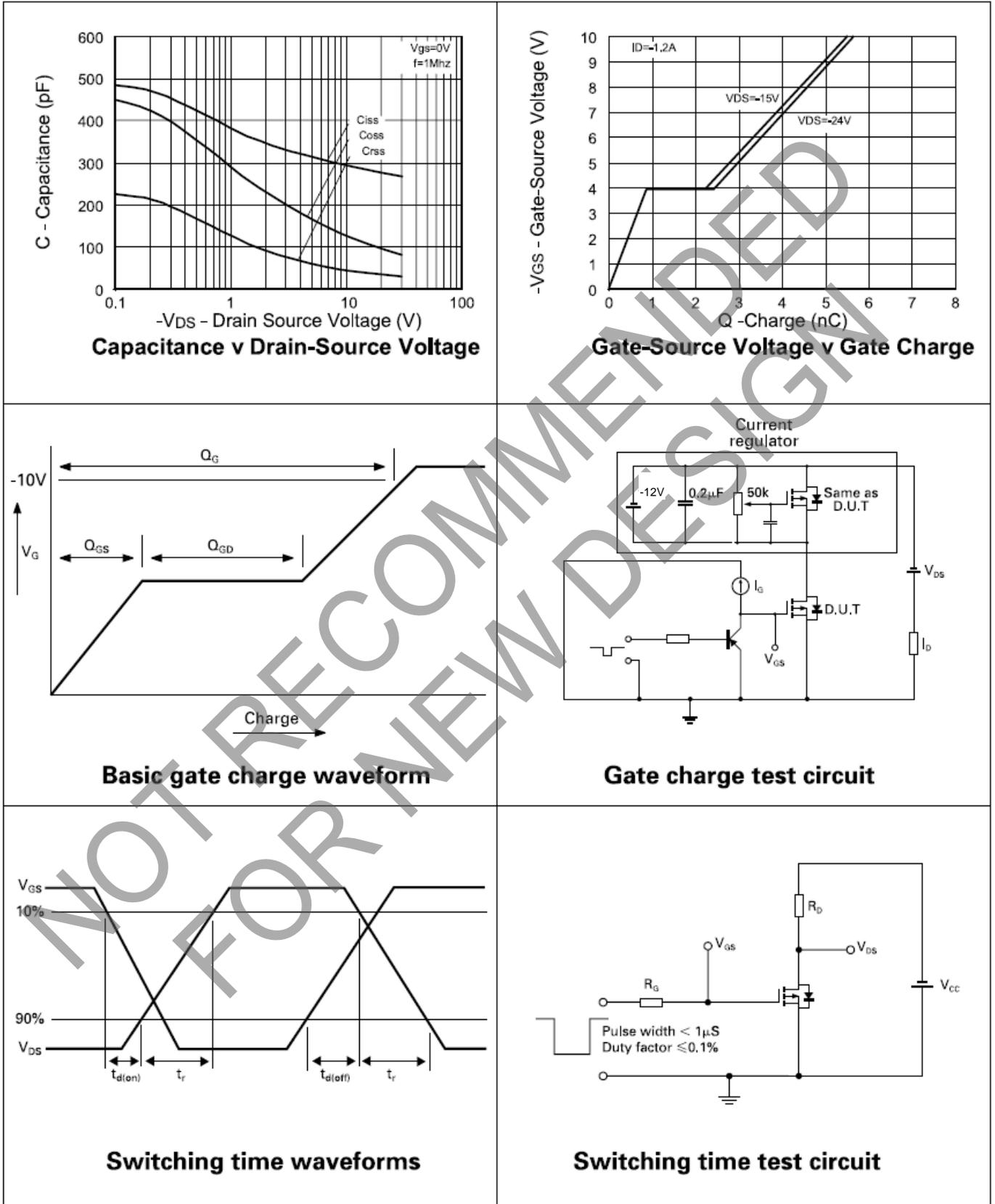
NOTES:

- (1) Measured under pulsed conditions. Width=300μs. Duty cycle ≤2%.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

Typical Characteristics



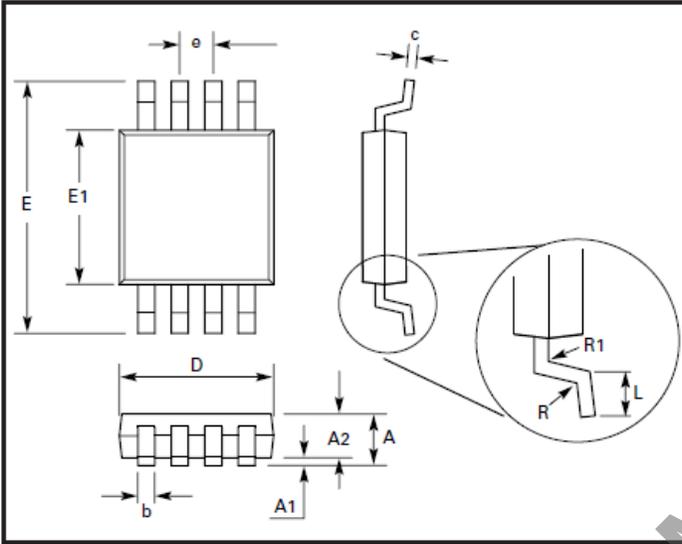
Typical Characteristics (Cont.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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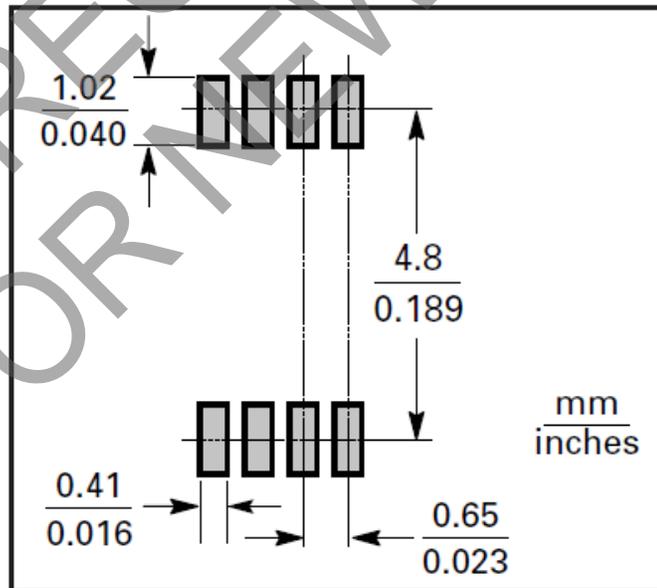


DIM	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.91	1.11	0.036	0.044
A1	0.10	0.20	0.004	0.008
B	0.25	0.36	0.010	0.014
C	0.13	0.18	0.005	0.007
D	2.95	3.05	0.116	0.120
e	0.65NOM		0.0256	
e1	0.33NOM		0.0128	
E	2.95	3.05	0.116	0.120
H	4.78	5.03	0.188	0.198
L	0.41	0.66	0.016	0.026
theta	0°	6°	0°	6°

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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